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Song et al.

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- (54) **LIQUID CRYSTAL DISPLAY**
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- (*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

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Related U.S. Application Data

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(30) **Foreign Application Priority Data**

Oct. 15, 2003 (KR) 10-2003-0071707

(51) **Int. Cl.**
G02F 1/1337 (2006.01)

(52) **U.S. Cl.** 349/129; 349/143

(58) **Field of Classification Search** 349/129
See application file for complete search history.

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(57) **ABSTRACT**

A liquid crystal display is provided, which includes: a first substrate; a first signal line formed on the first substrate; a second signal line formed on the first substrate and intersecting the first signal line; a thin film transistor connected to the first and the second signal lines; a pixel electrode connected to the thin film transistor; a second substrate; a common electrode formed on the second substrate; a liquid crystal layer interposed between the first substrate and the second substrate; and a tilt direction determining member formed on one of the first and the second substrates and having a notch.

12 Claims, 10 Drawing Sheets

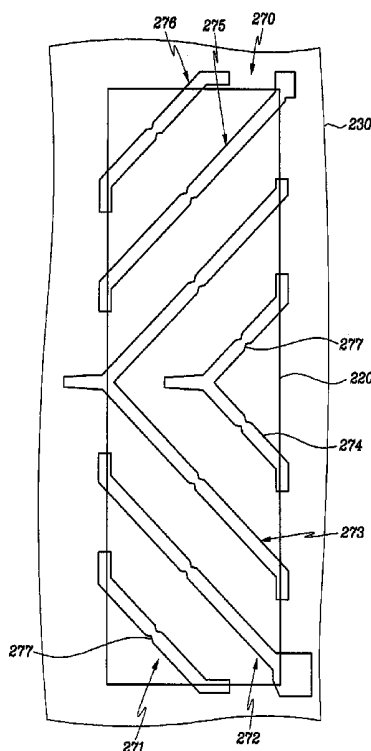


FIG.1

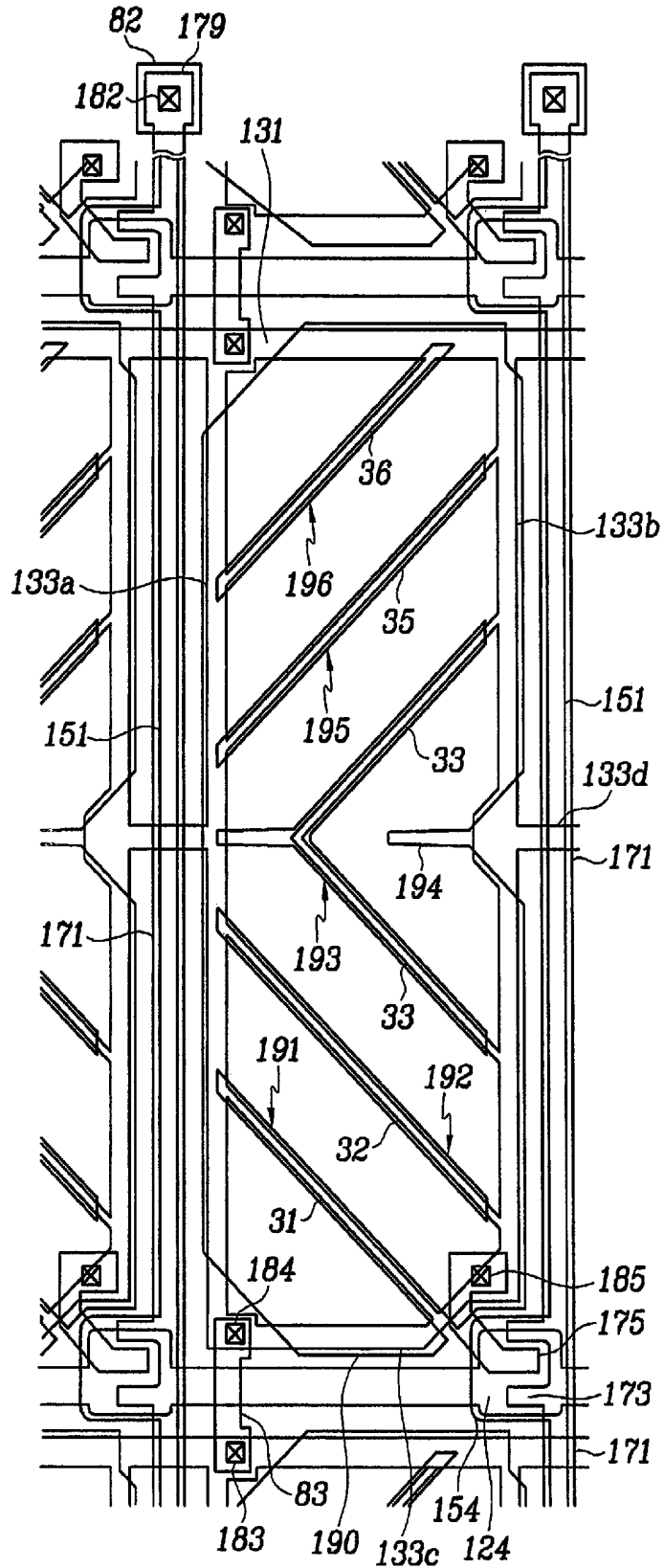


FIG.2

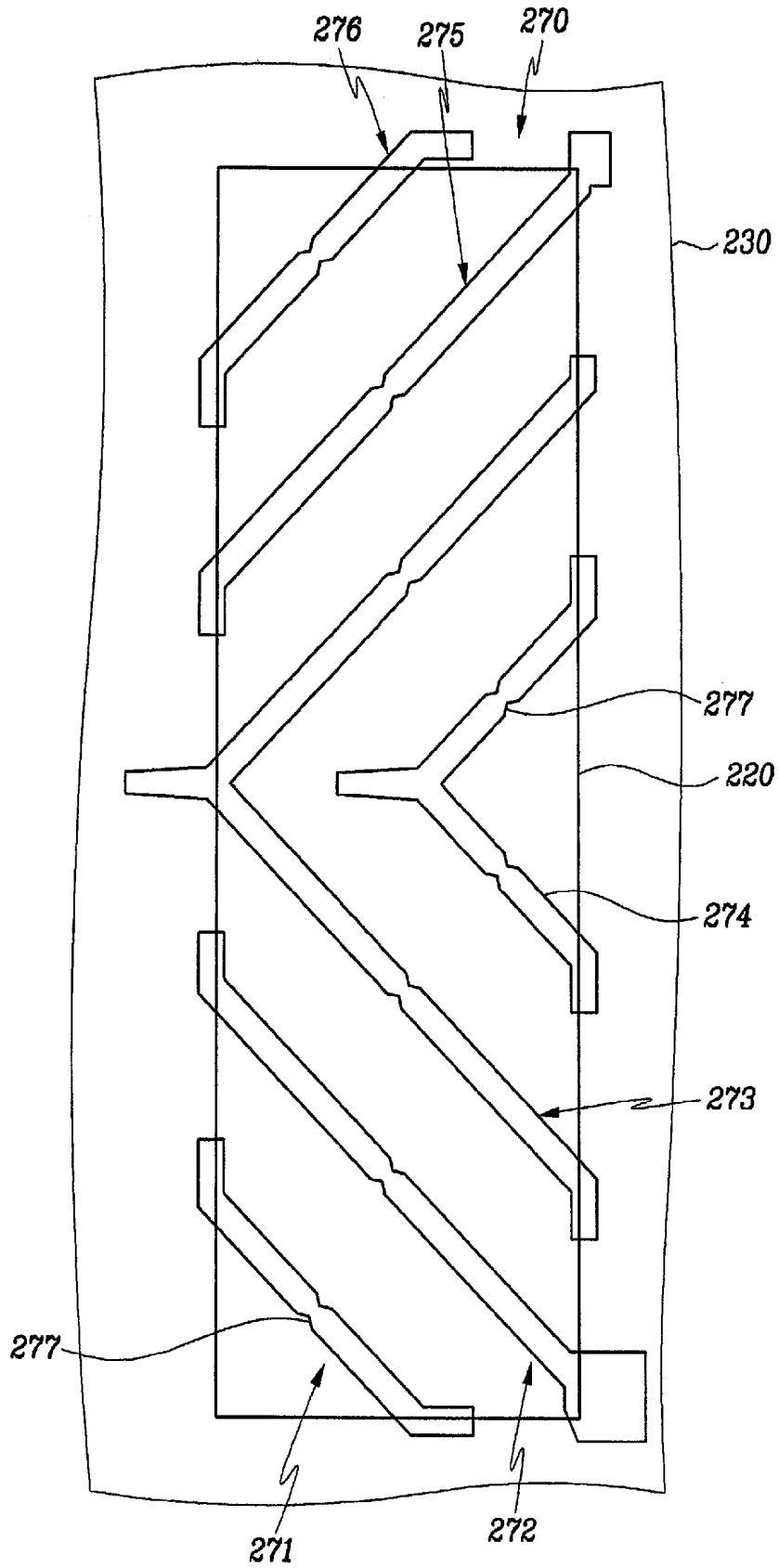


FIG.3

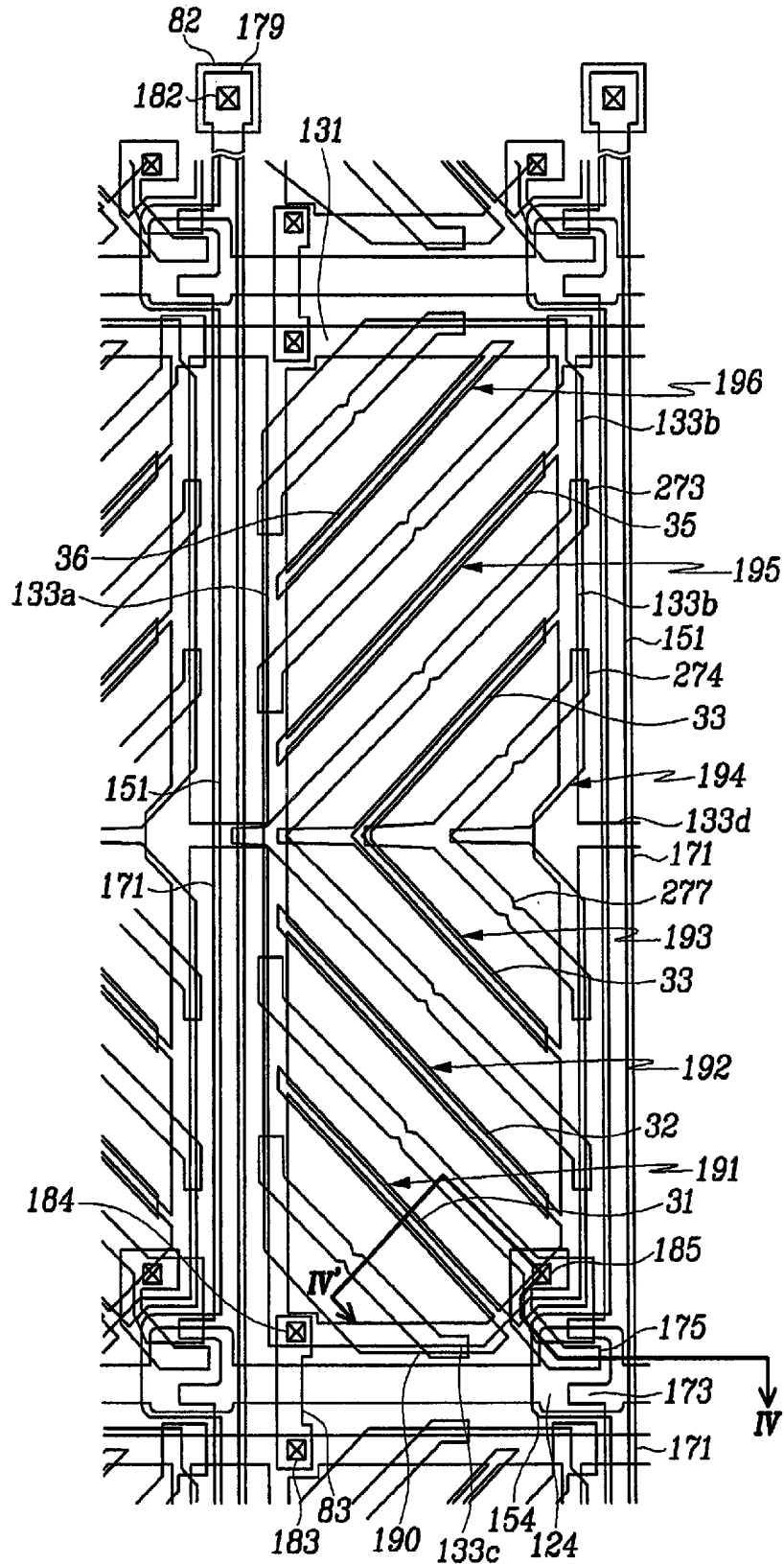


FIG.4

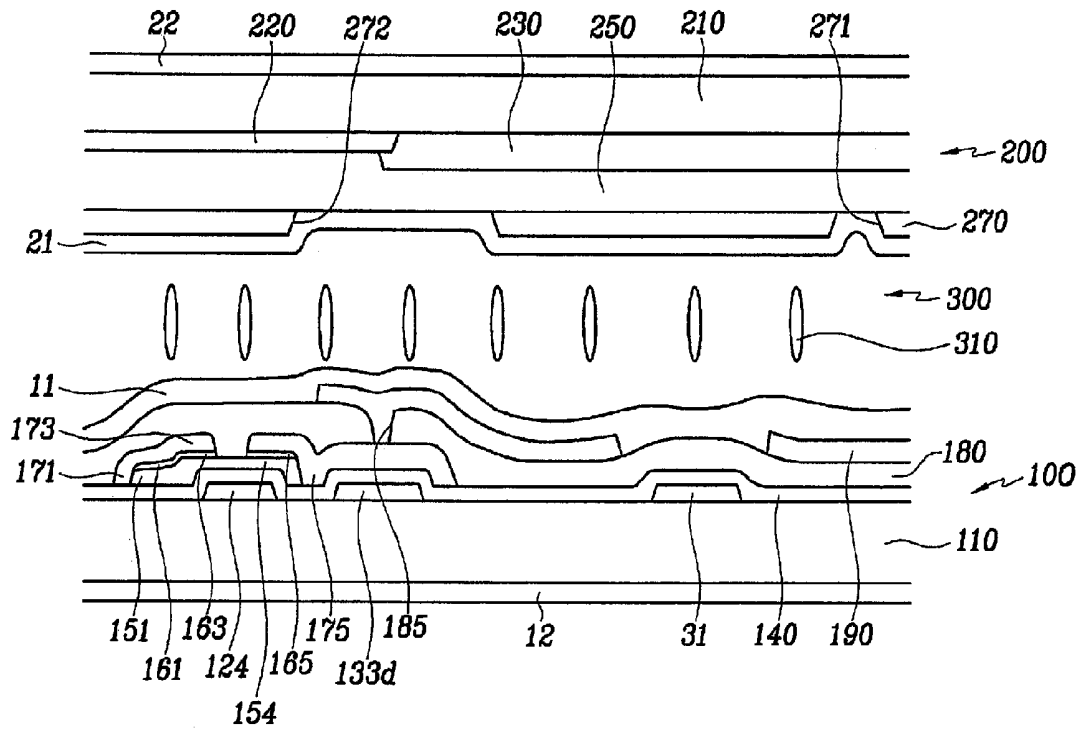


FIG.5A

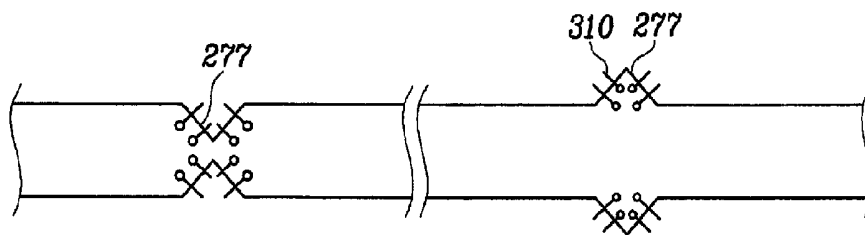


FIG.5B

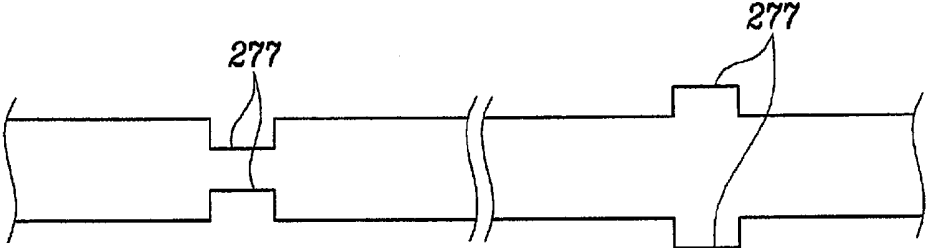


FIG.5C

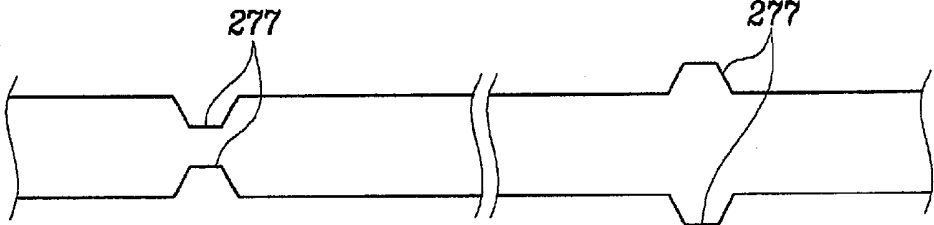


FIG.5D

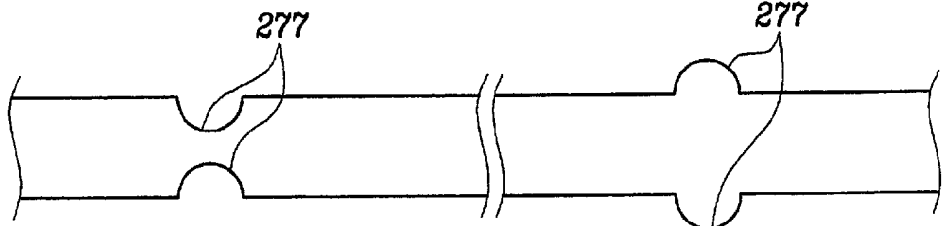


FIG. 6

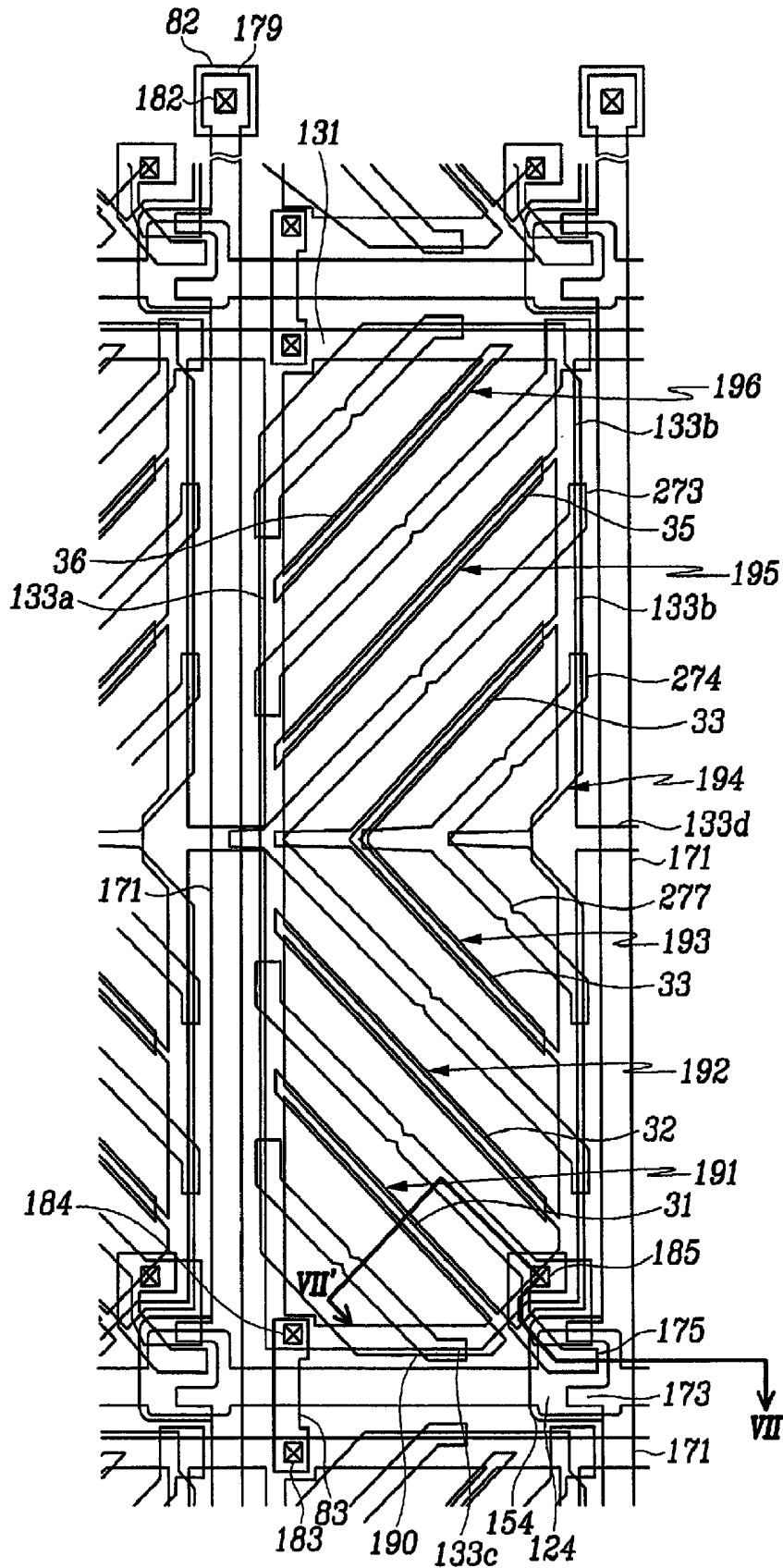


FIG. 7

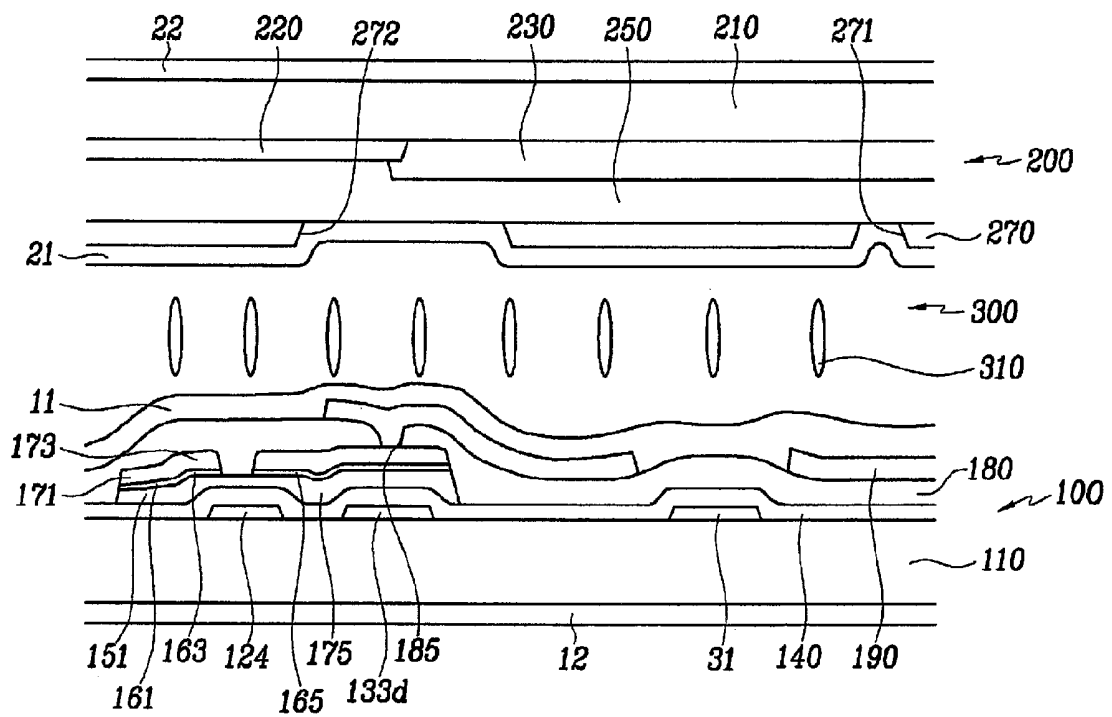


FIG.8

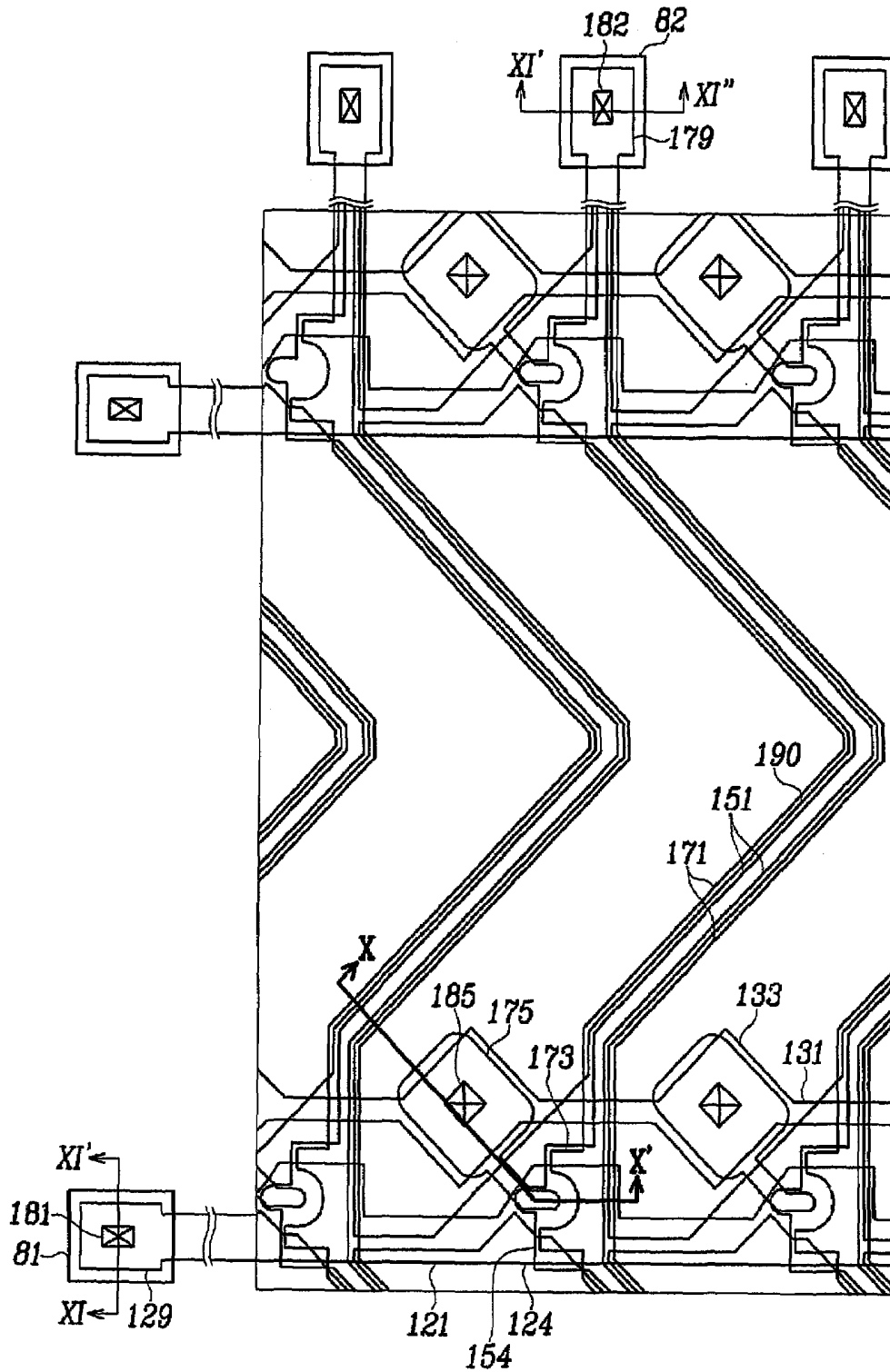


FIG. 9

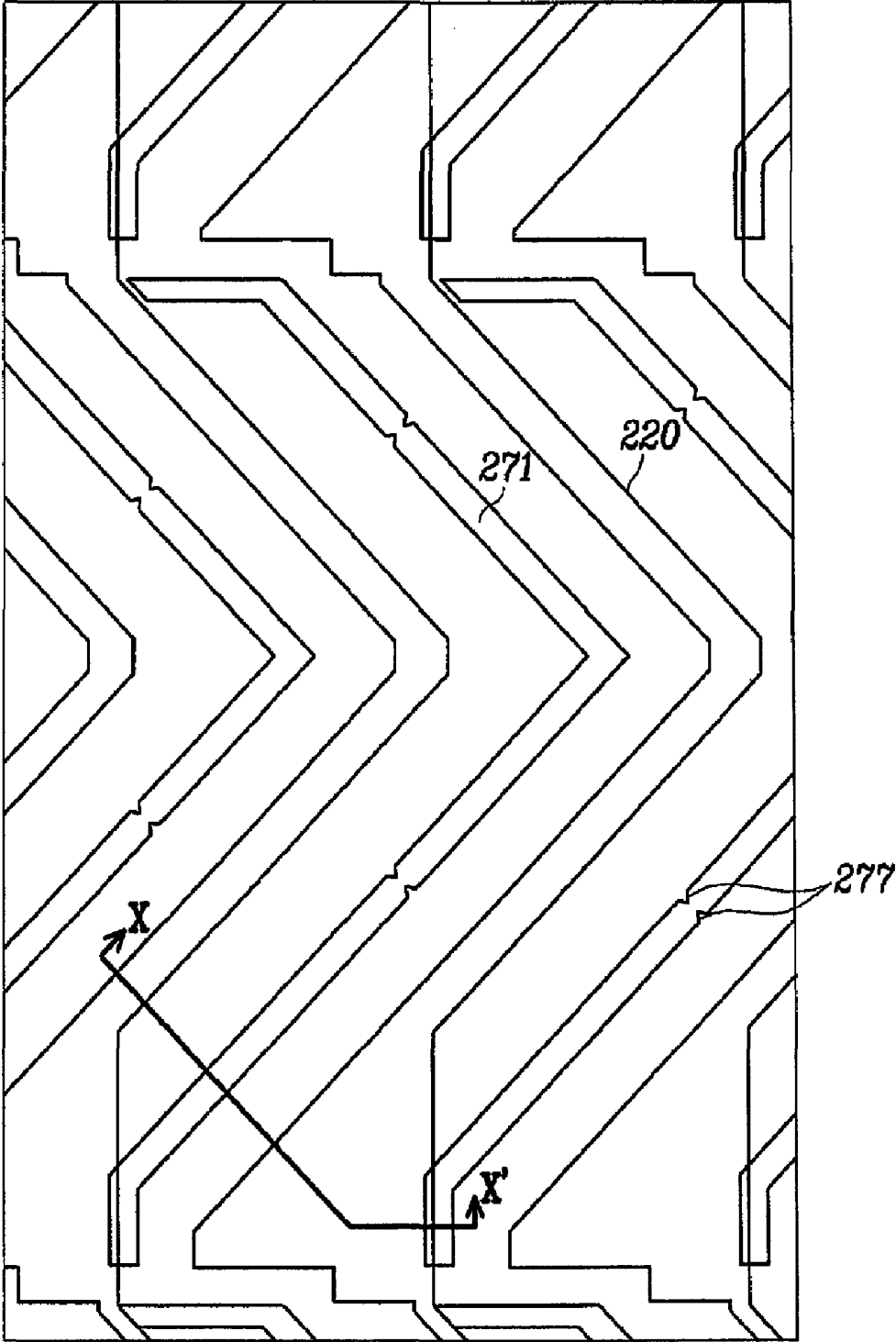


FIG.10

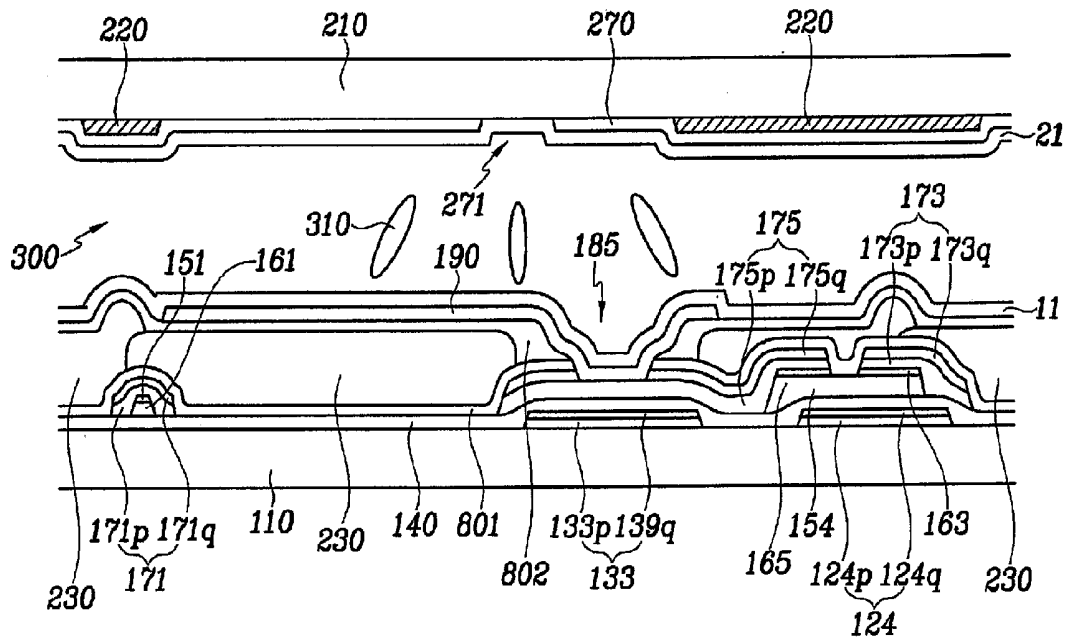
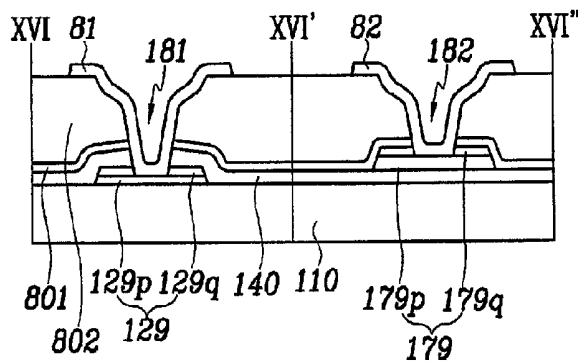


FIG.11



LIQUID CRYSTAL DISPLAY**CROSS-REFERENCE TO RELATED APPLICATIONS**

This application is a continuation of and claims the benefit of U.S. patent application Ser. No. 10/965,267 filed on Oct. 15, 2004, now U.S. Pat. No. 7,218,369 which claims priority to and the benefit of Korean Patent Application No. 10-2003-0071707 filed in the Korean Intellectual Property Office on Oct. 15, 2003, all of which are incorporated herein by reference.

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a liquid crystal display.

2. Description of the Related Art

A liquid crystal display (LCD) is one of the most widely used flat panel displays. An LCD includes two panels provided with field-generating electrodes such as pixel electrodes and a common electrode and a liquid crystal (LC) layer interposed therebetween. The LCD displays images by applying voltages to the field-generating electrodes to generate an electric field in the LC layer, which determines orientations of LC molecules in the LC layer to adjust polarization of incident light.

Among the LCDs, a vertical alignment (VA) mode LCD, which aligns LC molecules such that the long axes of the LC molecules are perpendicular to the panels in absence of electric field, is spotlighted because of its high contrast ratio and wide reference viewing angle that is defined as a viewing angle making the contrast ratio equal to 1:10 or as a limit angle for the inversion in luminance between the grays.

The wide viewing angle of the VA mode LCD can be realized by cutouts in the field-generating electrodes and protrusions on the field-generating electrodes. Since the cutouts and the protrusions can determine the tilt directions of the LC molecules, the tilt directions can be distributed into several directions by using the cutouts and the protrusions such that the reference viewing angle is widened.

However, the cutouts and the protrusions may yield spots or afterimages and the spots generated by scrubbing the LCD are remained. It is because the tilt directions of the liquid crystal molecules near the cutouts and the protrusions are determined by push of the liquid crystal molecules on the field-generating electrodes or by collision with them and thus the alignment of the liquid crystal molecules is unstable and irregular.

SUMMARY OF THE INVENTION

A motivation of the present invention is to solve the problems of the conventional art.

A liquid crystal display is provided, which includes: a first substrate; a first signal line formed on the first substrate; a second signal line formed on the first substrate and intersecting the first signal line; a thin film transistor connected to the first and the second signal lines; a pixel electrode connected to the thin film transistor; a second substrate; a common electrode formed on the second substrate; a liquid crystal layer interposed between the first substrate and the second substrate; and a tilt direction determining member formed on one of the first and the second substrates and having a notch.

The notch may be convex or concave and may be triangular, rectangular, trapezoidal, or semicircular.

The tilt direction determining member may have two opposite main edges facing each other and the notch may have an edge oblique to or perpendicular to the main edges of the tilt direction determining member.

5 The tilt direction determining member may include a cutout formed at the pixel electrode or the common electrode.

The cutout may have a width ranging about 8-10 microns.

The tilt direction determining member may include a protrusion.

10 The tilt direction determining member may have two opposite main edges facing each other and making an angle of about 45 degrees with the first signal line.

The liquid crystal display may further include first and second polarizers disposed on the first and the second substrates and having crossed transmissive axes.

The liquid crystal layer may have negative anisotropy and subjected to a vertical alignment.

15 The transmissive axis of one of the polarizers may be parallel to the first signal line.

The tilt direction determining member may have inversion symmetry with respect to a straight line bisecting the pixel electrode the transmissive axis of one of the polarizers are parallel to the first signal line.

20 The second signal line may include a curved portion and an intersecting portion connected to the curved portion and intersecting the gate line.

25 The curved portion of the data line may include a pair of rectilinear portions connected to each other and making an angle of about 45 degrees with the gate line.

The liquid crystal display may further include a third signal line separated from the first and the second signal lines and overlapping the pixel electrode.

30 The third signal line may overlap tilt direction determining member.

BRIEF DESCRIPTION OF THE DRAWINGS

40 The present invention will become more apparent by describing embodiments thereof in detail with reference to the accompanying drawings in which:

FIG. 1 is a layout view of a TFT array panel of an LCD according to an embodiment of the present invention;

45 FIG. 2 is a layout view of a common electrode panel of an LCD according to an embodiment of the present invention;

FIG. 3 is a layout view of an LCD including the TFT array panel shown in FIG. 1 and the common electrode panel shown in FIG. 2;

50 FIG. 4 is a sectional view of the LCD shown in FIG. 3 taken along the line IV-IV';

FIGS. 5A-5D illustrate various shapes of the notches shown in FIGS. 2 and 3;

55 FIG. 6 is a layout view of an LCD according to another embodiment of the present invention;

FIG. 7 is a sectional view of the LCD shown in FIG. 6 taken along the line VII-VII';

60 FIG. 8 is a layout view of a TFT array panel for an LCD according to an embodiment of the present invention;

FIG. 9 is a layout view of a common electrode panel for an LCD according to an embodiment of the present invention;

65 FIG. 10 is a sectional view of an LCD shown including the TFT array panel shown in FIG. 8 and the common electrode panel shown in FIG. 9 taken along the line X-X'; and

FIG. 11 is a sectional view of the LCD shown in FIG. 3 taken along the lines XI-XI' and XI'-XI''.

DETAILED DESCRIPTION OF EMBODIMENTS

The present invention now will be described more fully hereinafter with reference to the accompanying drawings, in which preferred embodiments of the invention are shown. The present invention may, however, be embodied in many different forms and should not be construed as limited to the embodiments set forth herein.

In the drawings, the thickness of layers, films and regions are exaggerated for clarity. Like numerals refer to like elements throughout. It will be understood that when an element such as a layer, film, region or substrate is referred to as being "on" another element, it can be directly on the other element or intervening elements may also be present. In contrast, when an element is referred to as being "directly on" another element, there are no intervening elements present.

Now, liquid crystal displays and thin film transistor (TFT) array panels for LCDs according to embodiments of the present invention will be described with reference to the accompanying drawings.

An LCD according to an embodiment of the present invention will be described in detail with reference to FIGS. 1-4.

FIG. 1 is a layout view of a TFT array panel of an LCD according to an embodiment of the present invention, FIG. 2 is a layout view of a common electrode panel of an LCD according to an embodiment of the present invention, FIG. 3 is a layout view of an LCD including the TFT array panel shown in FIG. 1 and the common electrode panel shown in FIG. 2, and FIG. 4 is a sectional view of the LCD shown in FIG. 3 taken along the line IV-IV'.

An LCD according to an embodiment of the present invention includes a TFT array panel 100 including pixel electrodes 190, TFTs, and signal lines 121, 131 and 171, a common electrode panel 200 including a common electrode 190, and a LC layer 300 interposed between the panels 100 and 200 and containing a plurality of LC molecules 310.

The TFT array panel 100 is now described in detail with reference FIGS. 1, 3 and 4.

A plurality of gate lines 121 and a plurality of storage electrode lines 131 are formed on an insulating substrate 110 such as transparent glass.

The gate lines 121 transmitting gate signals extend substantially in a transverse direction and are separated from each other. Each gate line 121 includes a plurality of projections forming a plurality of gate electrodes 124 and it may include an end portion having a large area for connection with a driving circuit that may be integrated into the TFT array panel 100 or mounted on the TFT array panel 100 in a form of integrated circuit chip.

Each storage electrode line 131 extends substantially in the transverse direction and includes a plurality of sets of a ring-shaped branch 133a-133c and oblique branches 31-36 connected to the ring-shaped branch 133a-133c and a plurality of branch connections 133d connected between adjacent branches 133a-133c. Each branch set includes a pair of first and second storage electrodes 133a and 133b extending in a longitudinal direction and a third storage electrode 133c connected to ends of the first and the second storage electrodes 133a and 133b and extending in the transverse direction and in an oblique direction. The oblique branches 31, 32, 35, 36 are connected to two of the first to the third storage electrodes 133a-133c. The oblique branch 33 obliquely runs from the second storage electrode 133b to the first storage electrode 133a and changes its course near a center of the first storage electrode 133a to return to the second storage electrode 133b. The storage electrode lines 131 are supplied with a predeter-

mined voltage such as a common voltage, which is applied to a common electrode 270 on the common electrode panel 200 of the LCD.

The gate lines 121 and the storage electrode lines 131 are preferably made of Al containing metal such as Al and Al alloy, Ag containing metal such as Ag and Ag alloy, Cu containing metal such as Cu and Cu alloy, Mo containing metal such as Mo and Mo alloy, Cr, Ti or Ta. The gate lines 121 and the storage electrode lines 131 may have a multi-layered structure including two films having different physical characteristics. One of the two films is preferably made of low resistivity metal including Al containing metal, Ag containing metal, and Cu containing metal for reducing signal delay or voltage drop in the gate lines 121 and the storage electrode lines 131. The other film is preferably made of material such as Cr, Mo and Mo alloy, Ta or Ti, which has good physical, chemical, and electrical contact characteristics with other materials such as indium tin oxide (ITO) or indium zinc oxide (IZO). Good examples of the combination of the two films are a lower Cr film and an upper Al—Nd alloy film and a lower Al film and an upper Mo film. The gate lines 121 and the storage electrode lines 131 may have a triple-layered structure including a lower Mo film, an intermediate Al film, and an upper Mo film.

In addition, the lateral sides of the gate lines 121 and the storage electrode lines 131 are inclined relative to a surface of the substrate, and the inclination angle thereof ranges about 30-80 degrees.

A gate insulating layer 140 preferably made of silicon nitride (SiNx) is formed on the gate lines 121 and the storage electrode lines 131.

A plurality of semiconductor stripes 151 preferably made of hydrogenated amorphous silicon (abbreviated to "a-Si") or polysilicon are formed on the gate insulating layer 140. Each semiconductor stripe 151 extends substantially in the longitudinal direction and has a plurality of projections 154 branched out toward the gate electrodes 124.

A plurality of ohmic contact stripes and islands 161 and 165 preferably made of silicide or n+ hydrogenated a-Si heavily doped with n type impurity such as phosphorous are formed on the semiconductor stripes 151. Each ohmic contact stripe 161 has a plurality of projections 163, and the projections 163 and the ohmic contact islands 165 are located in pairs on the projections 154 of the semiconductor stripes 151.

The lateral sides of the semiconductor stripes 151 and the ohmic contacts 161 and 165 are inclined relative to a surface of the substrate, and the inclination angles thereof are preferably in a range between about 30-80 degrees.

A plurality of data lines 171 and a plurality of drain electrodes 175 separated from the data lines 171 are formed on the ohmic contacts 161 and 165 and the gate insulating layer 140.

The data lines 171 for transmitting data voltages extend substantially in the longitudinal direction and intersect the gate lines 121 and the storage electrode lines 131. In particular, the data lines 171 intersect the branch connections 133d such that each data line 171 is disposed between adjacent two of the ring-shaped branches 133a-133c. Each data line 171 includes an end portion 179 having a large area for contact with another layer or an external device. A plurality of branches of each data line 171, which project toward the gate electrodes 124, form a plurality of curved (like a crescent) source electrodes 173. Each drain electrode 175 includes an end portion having a large area for contact with another layer and another end portion partly enclosed by a source electrode 173. A gate electrode 124, a source electrode 173, and a drain electrode 175 along with a projection 154 of a semiconductor

stripe **151** form a TFT having a channel formed in the projection **154** disposed between the source electrode **173** and the drain electrode **175**.

The data lines **171** and the drain electrodes **175** are preferably made of refractory metal such as Cr, Mo, Ti, Ti, or alloys thereof and they may also have a multilayered structure including a lower film (not shown) preferably made of refractory metal and an upper film (not shown) located thereon and preferably made of low resistivity material such as Al containing metal. Alternatively, the data lines **171**, etc., include triple layers interposing an intermediate layer of Al or Al alloy.

Like the gate lines **121** and the storage electrode lines **131**, the data lines **171** and the drain electrodes **175** have tapered lateral sides, and the inclination angles thereof range about 30-80 degrees.

The ohmic contacts **161** and **165** are interposed only between the underlying semiconductor stripes **151** and the overlying data lines **171** and the overlying drain electrodes **175** thereon and reduce the contact resistance therebetween. The semiconductor stripes **151** include a plurality of exposed portions, which are not covered with the data lines **171** and the drain electrodes **175**, such as portions located between the source electrodes **173** and the drain electrodes **175**.

A passivation layer **180** is formed on the data lines **171**, the drain electrodes **175**, and the exposed portions of the semiconductor stripes **151**. The passivation layer **180** is preferably made of photosensitive organic material having a good flatness characteristic, low dielectric insulating material having dielectric constant lower than 4.0 such as a-Si:C:O and a-Si:O:F formed by plasma enhanced chemical vapor deposition (PECVD), or inorganic material such as silicon nitride. The passivation layer **180** may include a lower film of inorganic insulator and an upper film of organic insulator.

The passivation layer **180** has a plurality of contact holes **182** and **185** exposing the end portions **179** of the data lines **171** and the end portions of the drain electrodes **175**, respectively. The passivation layer **180** and the gate insulating layer **140** have a plurality of contact holes **183** and **184** exposing upper left corners and lower left corners of the ring-type branches **133a-133c**, respectively.

A plurality of pixel electrodes **190**, a plurality of contact assistants **82**, and a plurality of overpasses **83**, which are preferably made of a transparent conductor such as ITO and IZO or a reflective conductor such as Al, are formed on the passivation layer **180**.

The pixel electrodes **190** are physically and electrically connected to the drain electrodes **175** through the contact holes **185** such that the pixel electrodes **190** receive the data voltages from the drain electrodes **175**.

The pixel electrodes **190** supplied with the data voltages generate electric fields in cooperation with the common electrode **270**, which determine the orientations of LC molecules **310** in the LC layer **300**.

A pixel electrode **190** and the common electrode **270** form a LC capacitor, which stores applied voltages after turn-off of the TFT. An additional capacitor called a "storage capacitor," which is connected in parallel to the LC capacitor, is provided for enhancing the voltage storing capacity. The storage capacitors are implemented by overlapping the pixel electrodes **190** with the storage electrode lines **131** including the storage electrodes **133a** and **133b**.

Each pixel electrode **190** is chamfered at its left corners and the chamfered edges of the pixel electrode **190** make an angle of about 45 degrees with the gate lines **121**.

Each pixel electrode **190** has a plurality of lower cutouts **191** and **192**, upper cutouts **195** and **196**, and center cutouts

193 and **194**, which partition the pixel electrode **190** into a plurality of partitions and overlap the oblique branches **31-36** of the storage electrode lines **131**. The oblique branches **31-36** can control texture that may be occur at intermediate positions of the cutouts **191-196**. The lower and the upper cutouts **191**, **192**, **195** and **196** are disposed at lower and upper halves of the pixel electrode **190**, respectively, and the center cutouts **193** and **194** are located between the lower cutouts **191** and **192** and the upper cutouts **195** and **196**. The cutouts **191-196** substantially have inversion symmetry with respect to an imaginary transverse center line bisecting the pixel electrode **190** into the upper and the lower halves.

The lower and the upper cutouts **191**, **192**, **195** and **196** make an angle of about 45 degrees to the gate lines **121**, and the upper cutouts **195** and **196**, which extend substantially parallel to each other and to the chamfered upper left edge of the pixel electrode **190**, extend substantially perpendicular to the lower cutouts **191** and **192**, which extend substantially parallel to each other.

The cutouts **191** and **196** extend approximately from a left longitudinal edge of the pixel electrode **190** approximately to transverse edges of the pixel electrode **190**. The cutouts **192** and **195** extend approximately from the left edge of the pixel electrode **190** approximately to a longitudinal right edge of the pixel electrode **190**.

The center cutout **193** includes a transverse portion extending approximately from the left edge of the pixel electrode **190** along the imaginary transverse line and a pair of oblique portions extending from the transverse portion to the right edge of the pixel electrode **190** and extending substantially parallel to the lower cutouts **191** and **192** and the upper cutouts **195** and **196**, respectively. The center cutout **194** extends along the transverse center line of the pixel electrode **190** and has an inlet from the right edge of the pixel electrode **190**, which has a pair of inclined edges substantially parallel to the lower cutouts **191** and **192** and the upper cutouts **195** and **196**, respectively.

Accordingly, the lower half of the pixel electrode **190** is partitioned into four lower partitions by the lower cutouts **191** and **192** and the center cutout **193**, and the upper half of the pixel electrode **190** is also partitioned into four upper partitions by the upper cutouts **195** and **196** and the center cutout **193**. The number of partitions or the number of the cutouts is varied depending on the design factors such as the size of pixels, the ratio of the transverse edges and the longitudinal edges of the pixel electrodes **190**, the type and characteristics of the LC layer **300**, and so on.

The contact assistants **82** are connected to the end portions **179** of the data lines **171** through the contact holes **182**. The contact assistants **82** protect the end portions **179** and complement the adhesion of the end portions **179** and external devices.

The overpasses **83** cross over the gate lines **121** and they are connected to the exposed portions of the storage electrode lines **131** through the contact holes **183** and **184** that are disposed opposite each other with respect to the gate lines **121**. A plurality of metal pieces (not shown) may be disposed on the gate insulating layer **140** opposite the gate lines **121** and the overpasses **83** may overlap the metal pieces or may be electrically connected to the metal pieces. The storage electrode lines **131** including the storage electrodes **133a-133c** along with the overpasses **83** and the metal pieces are used for repairing defects in the gate lines **121**, the data lines **171**, or the TFTs. The electrical connection between the gate lines **121** and the storage electrode lines **131** for repairing the gate lines **121** is obtained by illuminating the cross points of the gate lines **121** and the overpasses **83** by a laser beam to

electrically connect the gate lines **121** to the overpasses **83**. In this case, the metal pieces enhance the electrical connection between the gate lines **121** and the overpasses **83**.

The description of the common electrode panel **200** follows with reference to FIGS. **2-4**.

A light blocking member **220** called a black matrix for preventing light leakage is formed on an insulating substrate **210** such as transparent glass. The light blocking member **220** may include a plurality of openings that face the pixel electrodes **190** and it may have substantially the same shape as the pixel electrodes **190**.

A plurality of color filters **230** are formed on the substrate **210** and they are disposed substantially in the areas enclosed by the light blocking member **220**. The color filters **230** may extend substantially in the longitudinal direction along the pixel electrodes **190**. Each of the color filters **230** may represent one of the primary colors such as red, green and blue colors.

An overcoat **250** for preventing the color filters **230** from being exposed and for providing a flat surface is formed on the color filters **230** and the light blocking member **220**.

A common electrode **270** preferably made of transparent conductive material such as ITO and IZO is formed on the overcoat **250**.

The common electrode **270** has a plurality of sets of cutouts **271-276** having pairs of notches **277**, each pair of the notches facing each other.

A set of cutouts **271-276** face a pixel electrode **190** and include a plurality of lower and upper cutouts **271** and **272** and **275** and **276** and center cutouts **273** and **274**. Each of the cutouts **271-276** is disposed between adjacent cutouts **191-196** of the pixel electrode **190** or between a cutout **196** and a chamfered edge of the pixel electrode **190**. In addition, each of the cutouts **271-276** has at least an oblique portion extending parallel to the lower cutouts **191** and **192** or the upper cutouts **195** and **196** of the pixel electrode **190**. The cutouts **271-276** substantially have inversion symmetry with respect to an imaginary transverse line bisecting the pixel electrode **190**.

Each of the cutouts **271** and **276** has an oblique portion extending approximately from a left edge of the pixel electrode **190** approximately to a lower or upper edge of the pixel electrode **190** and transverse and longitudinal portions extending from respective ends of the oblique portion along edges of the pixel electrode **190**, overlapping the edges of the pixel electrode **190**, and making obtuse angles with the oblique portion.

Each of the cutouts **272** and **275** has an oblique portion, a longitudinal portion connected to an end of the oblique portion, and an expansion connected to the other end of the oblique portion. The oblique portion extends approximately from the left edge of the pixel electrode **190** approximately to lower right or upper right corner of the pixel electrode **190**. The longitudinal portion extends from the end of the oblique portion along the left edge of the pixel electrode **190**, overlaps the left edge of the pixel electrode **190**, and makes an obtuse angle with the oblique portion. The expansion covers the respective corner of the pixel electrode **190**.

The cutout **273** has a pair of oblique portions extending approximately from the center of the left edge of the pixel electrode **190** to the right edge of the pixel electrode **190**, a transverse portion extending from a meeting point of the oblique portions to the left, and a pair of longitudinal portions extending from the respective oblique portions along the right edge of the pixel electrode **190**, overlapping the right edge of the pixel electrode **190**, and making an obtuse angle with the respective oblique portions. The cutout **274** has a transverse

portion extending along the transverse center line of the pixel electrode **190**, a pair of oblique portions extending from the transverse portion approximately to the right edge of the pixel electrode **190** and making obtuse angles with the transverse portion, and a pair of longitudinal portions extending from the respective oblique portions along the right edge of the pixel electrode **190**, overlapping the right edge of the pixel electrode **190**, and making an obtuse angle with the respective oblique portions.

The number of the cutouts **271-276** may be varied depending on the design factors, and the light blocking member **220** may also overlap the cutouts **271-276** to block the light leakage through the cutouts **271-276**.

Alignment layers **11** and **21** that may be homeotropic are coated on inner surfaces of the panels **100** and **200**, and polarizers **12** and **22** are provided on outer surfaces of the panels **100** and **200** such that their polarization axes may be crossed and one of the transmissive axes may be parallel to the gate lines **121**. One of the polarizers may be omitted when the LCD is a reflective LCD.

The LCD may further include at least one retardation film for compensating the retardation of the LC layer **300**.

It is preferable that the LC layer **300** has negative dielectric anisotropy and it is subjected to a vertical alignment that the LC molecules **310** in the LC layer **300** are aligned such that their long axes are substantially vertical to the surfaces of the panels **100** and **200** in absence of electric field.

As shown in FIG. **3**, a set of the cutouts **191-196** and **271-276** divides a pixel electrode **190** into a plurality of sub-areas and each sub-area has two major edges.

The cutouts **191-196** and **271-276** as well as the trenches **186** control the tilt directions of the LC molecules **310** in the LC layer **300**. This will be described in detail.

The cutouts **191-196** and **271-276** control the tilt directions of the LC molecules in the LC layer **3**. This will be described in detail.

Upon application of the common voltage to the common electrode **270** and a data voltage to the pixel electrodes **190**, an electric field substantially perpendicular to the surfaces of the panels **100** and **200** is generated. The LC molecules tend to change their orientations in response to the electric field such that their long axes are perpendicular to the field direction.

The cutouts **191-196** and **271-276** of the electrodes **190** and **270** and the edges of the pixel electrodes **190** distort the electric field to have a horizontal component that is substantially perpendicular to the edges of the cutouts **191-196** and **271-276** and the edges of the pixel electrodes **190**. Accordingly, the LC molecules on each sub-area are tilt in a direction by the horizontal component and the azimuthal distribution of the tilt directions are localized to four directions, thereby increasing the viewing angle of the LCD.

In the meantime, the horizontal components generated by opposite edges of a cutout **191-196** or **271-275** are antiparallel and they may be nearly destructed. Accordingly, the tilt directions of the LC molecules **310** in the cutouts **191-196** and **271-275** are nearly random, thereby causing texture. A notch **277** of a cutout **271-276** generates a secondary horizontal component to determine the orientations of the LC molecules **310** disposed near the cutouts **271-276**. For example, the LC molecules **310** disposed near a notch **277** in a cutout **271-276** tend to tilt in a direction perpendicular to an edge of the notch **277**. Therefore, the LC molecules **310** in the cutouts **271-276** can tilt in a direction determined by the notches **277** and the texture may be reduced.

At least one of the cutouts **191-196** and **271-276** can be substituted with protrusions or depressions made of organic

or inorganic material and the notches 277 can be also provided at the protrusions and the depressions.

The shapes and the arrangements of the cutouts 191-196 and 271-276 and the notches 277 may be modified.

FIGS. 5A-5D illustrate various shapes of the notches shown in FIGS. 2 and 3.

Referring to FIGS. 5A-5D, the notches 277 are triangular, rectangular, trapezoidal, or semicircular and they are convex or concave. As described above, the LC molecules 310 near the notches 277 are aligned such that their long axes are perpendicular to edges of the notches 277 and almost all the LC molecules in the cutouts 271-276 exhibit stable alignment. Accordingly, width of the cutouts 271-276 can be remained in a range of about 8-10 microns.

Several notches 277 may be provided at one cutout 271-276 and the convex notches and the concave notches may be alternately arranged. The notches 277 may be provided either or both of the pixel electrodes 190 and the common electrode 270.

An LCD according to another embodiment of the present invention will be described in detail with reference to FIGS. 6 and 7.

FIG. 6 is a layout view of an LCD according to another embodiment of the present invention, and FIG. 7 is a sectional view of the LCD shown in FIG. 6 taken along the line VII-VII'.

Referring to FIGS. 6 and 7, an LCD according to this embodiment also includes a TFT array panel 100, a common electrode panel 200, and a LC layer 300 interposed therebetween. Layered structures of the panels 100 and 200 according to this embodiment are almost the same as those shown in FIGS. 1-4.

Regarding the TFT array panel 100, a plurality of gate lines 121 including a plurality of gate electrodes 124 and a plurality of storage electrode lines 131 including a plurality of ring-shaped branches 133a-133c, oblique branches 31-36, and connections 133d are formed on a substrate 110, and a gate insulating layer 140, a plurality of semiconductor stripes 151 including a plurality of projections 154, and a plurality of ohmic contact stripes 161 including a plurality of projections 163 and a plurality of ohmic contact islands 165 are sequentially formed thereon. A plurality of data lines 171 including a plurality of source electrodes 173 and a plurality of drain electrodes 175, are formed on the ohmic contacts 161 and 165, and a passivation layer 180 are formed thereon. A plurality of contact holes 182 and 185 are provided at the passivation layer 180, and a plurality of pixel electrodes 190 and a plurality of contact assistants 82 are formed on the passivation layer 180. An alignment layer 11 and a polarizer 12 are disposed on inner and outer surfaces of the TFT array panel 100.

Regarding the common electrode panel 200, a light blocking member 220, a plurality of color filters 230, an overcoat 250, a common electrode 270 having cutouts 275-277 to having notches 277, and an alignment layer 21 are formed on an insulating substrate 210. An alignment layer 21 and a polarizer 22 are disposed on inner and outer surfaces of the common electrode panel 200.

Different from the TFT array panel 100 shown in FIGS. 1, 3 and 4, the semiconductor stripes 151 of the TFT array panel 100 according to this embodiment have almost the same planar shapes as the data lines 171 and the drain electrodes 175 as well as the underlying ohmic contacts 161 and 165. However, the projections 154 of the semiconductor stripes 151 include some exposed portions, which are not covered

with the data lines 171 and the drain electrodes 175, such as portions located between the source electrodes 173 and the drain electrodes 175.

A manufacturing method of the TFT array panel 100 according to an embodiment simultaneously forms the data lines 171, the drain electrodes 175, the metal pieces 172, the semiconductors 151, and the ohmic contacts 161 and 165 using one photolithography process.

A photoresist pattern for the photolithography process has position-dependent thickness, and in particular, it has first and second portions with decreased thickness. The first portions are located on wire areas that will be occupied by the data lines 171, the drain electrodes 175, and the metal pieces 172 and the second portions are located on channel areas of TFTs.

The position-dependent thickness of the photoresist is obtained by several techniques, for example, by providing translucent areas on the exposure mask as well as transparent areas and light blocking opaque areas. The translucent areas may have a slit pattern, a lattice pattern, a thin film(s) with intermediate transmittance or intermediate thickness. When using a slit pattern, it is preferable that the width of the slits or the distance between the slits is smaller than the resolution of a light exposer used for the photolithography. Another example is to use reflowable photoresist. In detail, once a photoresist pattern made of a reflowable material is formed by using a normal exposure mask only with transparent areas and opaque areas, it is subject to reflow process to flow onto areas without the photoresist, thereby forming thin portions.

As a result, the manufacturing process is simplified by omitting a photolithography step.

Many of the above-described features of the LCD shown in FIGS. 1-4 may be appropriate to the TFT array panel shown in FIGS. 6 and 7.

An LCD according to another embodiment of the present invention is described in detail with reference to FIGS. 8-11.

FIG. 8 is a layout view of a TFT array panel for an LCD according to an embodiment of the present invention, FIG. 9 is a layout view of a common electrode panel for an LCD according to an embodiment of the present invention, FIG. 10 is a sectional view of an LCD shown including the TFT array panel shown in FIG. 8 and the common electrode panel shown in FIG. 9 taken along the line X-X', and FIG. 11 is a sectional view of the LCD shown in FIG. 3 taken along the lines XI-XI' and XI'-XI''.

An LCD according to this embodiment includes a TFT array panel 100, a common electrode panel 200 facing the TFT array panel 100, and a LC layer 300 interposed between the TFT array panel 100 and the common electrode panel 200.

The TFT array panel 100 is now described in detail with reference to FIGS. 8, 10 and 11.

A plurality of gate lines 121 and a plurality of storage electrode lines 131 are formed on an insulating substrate 110.

The gate lines 121 extend substantially in a transverse direction and are separated from each other. Each gate line 121 includes a plurality of projections forming a plurality of gate electrodes 124 and an end portion 129 having a large area for contact with another layer or an external device.

Each storage electrode line 131 extends substantially in the transverse direction and includes a plurality of projections forming storage electrodes 133. Each storage electrode 133 has a shape of a diamond or a rectangle rotated by about 45 degrees and it is located close to the lower of adjacent two of the gate lines 121. The storage electrode lines 131 are supplied with a predetermined voltage such as a common voltage, which is applied to a common electrode 270 on the common electrode panel 200 of the LCD.

The gate lines **121** and the storage electrode lines **131** have a double-layered structure including two films having different physical characteristics, a lower film and an upper film. The upper film is preferably made of low resistivity metal including Al containing metal such as Al and Al alloy, Ag containing metal such as Ag and Ag alloy, or Cu containing metal such as Cu and Cu alloy for reducing signal delay or voltage drop in the gate lines **121** and the storage electrode lines **131**. On the other hand, the lower film is preferably made of material such as Cr, Mo, Mo alloy, Ta, or Ti, which has good physical, chemical, and electrical contact characteristics with other materials such as indium tin oxide (ITO) or indium zinc oxide (IZO). A good exemplary combination of the lower film material and the upper film material is Cr and Al—Nd alloy. In FIGS. **10** and **11**, the lower and the upper films of the gate electrodes **124** are indicated by reference numerals **124p** and **124q**, respectively, the lower and the upper films of the end portions **129** are indicated by reference numerals **129p** and **129q**, respectively, and the lower and the upper films of the storage electrodes **133** are indicated by reference numerals **133p** and **133q**, respectively. Portions of the upper film **129q** of the end portions **129** of the gate lines **121** are removed to expose the underlying portions of the lower films **129p**.

Alternatively, the gate lines **121** and the storage electrode lines **131** may include an upper film having a good contact characteristic and a lower film having low resistivity and an example thereof is a Mo upper film and an Al lower film. Furthermore, the gate lines **121** and the storage electrode lines **131** may have a single layer structure preferably including Al containing metal, Ag containing metal, Cu containing metal, Mo containing metal, Cr, Ti or Ta or may include three or more layers.

In addition, the lateral sides of the gate lines **121** and the storage electrode lines **131** are inclined relative to a surface of the substrate **110**, and the inclination angle thereof ranges about 30-80 degrees.

A gate insulating layer **140** preferably made of silicon nitride (SiNx) is formed on the gate lines **121** and the storage electrode lines **131**.

A plurality of semiconductor stripes **151** preferably made of hydrogenated amorphous silicon (abbreviated as "a-Si") or polysilicon are formed on the gate insulating layer **140**. Each semiconductor stripe **151** extends substantially in the longitudinal direction while it is curved periodically. Each semiconductor stripe **151** has a plurality of projections **154** branched out toward the gate electrodes **124**.

A plurality of ohmic contact stripes and islands **161** and **165** preferably made of silicide or n+hydrogenated a-Si heavily doped with n type impurity such as phosphorous (P) are formed on the semiconductor stripes **151**. Each ohmic contact stripe **161** has a plurality of projections **163**, and the projections **163** and the ohmic contact islands **165** are located in pairs on the projections **154** of the semiconductor stripes **151**.

The lateral sides of the semiconductor stripes **151** and the ohmic contacts **161** and **165** are inclined relative to the surface of the substrate **110**, and the inclination angles thereof are preferably in a range between about 30-80 degrees.

A plurality of data lines **171** and a plurality of drain electrodes **175** separated from each other are formed on the ohmic contacts **161** and **165** and the gate insulating layer **140**.

The data lines **171** for transmitting data voltages extend substantially in the longitudinal direction and intersect the gate lines **121** and the storage electrode lines **131**. Each data line **171** has an end portion **179** having a large area for contact with another layer or an external device and it includes a

plurality of pairs of oblique portions and a plurality of longitudinal portions such that it curves periodically. A pair of oblique portions are connected to each other to form a chevron and opposite ends of the pair of oblique portions are connected to respective longitudinal portions. The oblique portions of the data lines **171** make an angle of about 45 degrees with the gate lines **121**, and the longitudinal portions cross over the gate electrodes **124**. The length of a pair of oblique portions is about one to nine times the length of a longitudinal portion, that is, it occupies about 50-90 percents of the total length of the pair of oblique portions and the longitudinal portion.

Each longitudinal portion of the data lines **171** includes a plurality of branches, which project towards the gate electrodes **124** to form curved (like a crescent) source electrodes **173**. Each drain electrode **175** includes a rectangular or rhombic expanded end portion, which has a large area for contact with another layer and overlaps a storage electrode **133**, and another end portion partly enclose by a source electrode **173**. The edges of the expansions of the drain electrode **175** are substantially parallel to the edges of the storage electrodes **133**. Each set of a gate electrode **124**, a source electrode **173**, and a drain electrode **175** along with a projection **154** of a semiconductor stripe **151** form a TFT having a channel formed in the semiconductor projection **154** disposed between the source electrode **173** and the drain electrode **175**.

The data lines **171** and the drain electrodes **175** also include a lower film **171p** and **175p** preferably made of refractory metal such as Cr, Mo, Ti, Ta, or alloys thereof and an upper film **171q** and **175q** located thereon and preferably made of Al containing metal, Ag containing metal, or Cu containing metal. In FIGS. **10** and **11**, the lower and the upper films of the source electrodes **173** are indicated by reference numerals **173p** and **173q**, respectively, and the lower and the upper films of the end portions **179** of the data lines **171** are indicated by reference numerals **179p** and **179q**, respectively. Portion of the upper films **179q** and **175q** of the expansions **179** of the data lines **171** and the drain electrodes **175** are removed to expose the underlying portions of the lower films **179p** and **175p**.

Like the gate lines **121** and the storage electrode lines **131**, the data lines **171** and the drain electrodes **175** have inclined lateral sides, and the inclination angles thereof range about 30-80 degrees.

The ohmic contacts **161** and **165** are interposed only between the underlying semiconductor stripes **151** and the overlying data lines **171** and the overlying drain electrodes **175** thereon and reduce the contact resistance therebetween.

A lower passivation film **801** preferably made of silicon nitride or silicon oxide is formed on the data lines **171** and the drain electrodes **175**, and exposed portions of the semiconductor stripes **151**, which are not covered with the data lines **171** and the drain electrodes **175**.

A plurality of color filter stripes **230** are formed on the lower passivation film **801**. Each of the color filter stripes **230** are disposed substantially between adjacent two the data lines **171** and extends substantially in the longitudinal direction, while it curves periodically. The color filter stripes **230** have a plurality of openings at the drain electrodes **175** and they are not disposed on a peripheral area which is provided with the end portions **129** of the gate lines **121** and the end portions **179** of the data lines **171**. Each of the color filter stripes **230** represents one of three primary colors such as red, green and blue and the colors are arranged in turn in the transverse direction. Adjacent two of the color filter stripes **230** representing different colors overlap each other to enhance the blocking of light leakage, but they may have coincident edges

or may be spaced apart from each other. The overlapping portions of the color filter stripes **230** form hills extending along the data lines **171**.

An upper passivation film **802** is formed on the color filter stripes **230** and one of the lower and the upper passivation films **801** and **802** may be omitted. The upper passivation film **802** is preferably made of photosensitive organic material having a good flatness characteristic or low dielectric insulating material such as a-Si:C:O and a-Si:O:F formed by plasma enhanced chemical vapor deposition (PECVD). However, the upper passivation film **802** may be also made of inorganic material. The upper insulating film **802** protrudes upward on the hills formed by the color filter stripes **230** such that the protrusions of the upper insulating layer **802** enhance the control of the tilt directions of the LC molecules **310** in the LC layer **300**.

The passivation films **801** and **802** have a plurality of contact holes **182** and **185** exposing the end portions **179** of the data lines **171** and the drain electrodes **175**, respectively, and the contact holes **185** is smaller than the openings of the color filter stripes **230**. The passivation films **801** and **802** and the gate insulating layer **140** have a plurality of contact holes **182** exposing the end portions **129** of the gate lines **121**. The sidewalls of the contact holes **181**, **182** and **185** are inclined with an angle of about 30-85 degrees or have stepwise profiles.

A plurality of pixel electrodes **190** and a plurality of contact assistants **81** and **82**, which are preferably made of ITO or IZO, are formed on the upper passivation film **802**. Alternatively, the pixel electrodes **190** may be made of transparent conductive polymer, and, for a reflective LCD, the pixel electrodes **190** are made of opaque reflective metal such as Cr. In these cases, the contact assistants **81** and **82** may be made of material such as ITO or IZO different from the pixel electrodes **190**.

Each pixel electrode **190** is located substantially in an area enclosed by the data lines **171** and the gate lines **121**, and thus it also forms a chevron. The pixel electrodes **190** cover the storage electrode lines **131** including the storage electrodes **133** and the expansions of the drain electrodes **175** and have chamfered edges substantially parallel to edges of the storage electrodes **133** that are close to the chamfered edges.

The pixel electrodes **190** are physically and electrically connected to the drain electrodes **175** through the contact holes **185** such that the pixel electrodes **190** receive the data voltages from the drain electrodes **175**.

The pixel electrodes **190** overlap the storage electrode lines **131** to form storage capacitors. The capacitances of the storage capacitors, i.e., the storage capacitances are increased by providing the projections (i.e., the storage electrodes **133**) at the storage electrode lines **131**, elongating the drain electrodes **175** connected to the pixel electrodes **190**, and providing the expansions at the drain electrodes **175** overlapping the storage electrodes **133** of the storage electrode lines **131** for decreasing the distance between the terminals and increasing the overlapping areas.

The pixel electrodes **190** overlap the data lines **171** as well as the gate lines **121** to increase aperture ratio.

The contact assistants **81** and **82** are connected to the exposed end portions **129** of the gate lines **121** and the exposed end portions **179** of the data lines **171** through the contact holes **181** and **182**, respectively. The contact assistants **81** and **82** protect the exposed portions **129** and **179** and complement the adhesiveness of the exposed portions **129** and **179** and external devices.

Finally, an alignment layer **11** that may be homeotropic is formed on the pixel electrodes **190** and the upper passivation film **802**.

The description of the common electrode panel **200** follows with reference to FIGS. 9-11.

A light blocking member **220** is formed on an insulating substrate **210** such as transparent glass and it includes a plurality of oblique portions facing the oblique portions of the data lines **171** and a plurality of right-angled-triangular portions facing the TFTs and the longitudinal portions of the data lines **171** such that the light blocking member **220** prevents light leakage between the pixel electrodes **190** and defines open areas facing the pixel electrodes **190**. Each of the triangular portions of the light blocking member **220** has a hypotenuse parallel to a chamfered edge of a pixel electrode **190**.

A common electrode **270** preferably made of transparent conductive material such as ITO and IZO is formed on the light blocking member **220** and the substrate **210**. The common electrode **270** is supplied with the common voltage and it has a plurality of chevron-like cutouts **271** having notches **277**.

Each cutout **271** includes a pair of oblique portions connected to each other, a transverse portion connected to one of the oblique portions, and a longitudinal portion connected to the other of the oblique portions. The oblique portions of the cutout **271** extend substantially parallel to the oblique portions of the data lines **171** and face a pixel electrode **190** so that they may bisect the pixel electrode **190** into left and right halves. The transverse and the longitudinal portions of the cutout **271** are aligned with transverse and longitudinal edges of the pixel electrode **190**, respectively, and they make obtuse angles with the oblique portions of the cutout **271**. The cutouts **271** are provided for controlling the tilt directions of the LC molecules **310** in the LC layer **300** and preferably have a width in a range between about 9-12 microns. The cutouts **271** may be substituted with protrusions preferably made of organic material and preferably having width ranging about 5 microns to 10 microns.

An alignment layer **21** that may be homeotropic is coated on the common electrode **270**.

A pair of polarizers (not shown) are provided on outer surfaces of the panels **100** and **200** such that their transmissive axes are crossed and one of the transmissive axes is parallel to the gate lines **121**. One of the polarizers may be omitted when the LCD is a reflective LCD.

The LCD may further include at least one retardation film for compensating the retardation of the LC layer **300**.

It is preferable that the LC layer **300** has negative dielectric anisotropy and it is subjected to a vertical alignment that the LC molecules **310** in the LC layer **300** are aligned such that their long axes are substantially vertical to the surfaces of the panels **100** and **200** in absence of electric field.

Upon application of the common voltage to the common electrode **270** and a data voltage to the pixel electrodes **190**, a primary electric field substantially perpendicular to the surfaces of the panels **100** and **200** is generated. The LC molecules **310** tend to change their orientations in response to the electric field such that their long axes are perpendicular to the field direction. In the meantime, the cutouts **271** of the common electrode **270** and the edges of the pixel electrodes **190** distort the primary electric field to have a horizontal component which determines the tilt directions of the LC molecules **310**. The horizontal component of the primary electric field is perpendicular to the edges of the cutouts **271** and the edges of the pixel electrodes **190**.

Accordingly, four sub-regions having different tilt directions, which are partitioned by edges of a pixel electrode **190**,

a cutout **271** bisecting the pixel electrode **190**, and an imaginary transverse center line passing through the meeting point of the oblique portions of the cutout **271**, are formed in a pixel region of the LC layer **300**, which are located on the pixel electrode **190**. Each sub-region has two major edges defined by the cutout **271** and an oblique edge of the pixel electrode **190**, respectively. The sub-regions are classified into a plurality of, preferably four, domains based on the tilt directions.

In the meantime, the direction of a secondary electric field due to the voltage difference between the pixel electrodes **190** is perpendicular to the edges of the cutouts **271**. Accordingly, the field direction of the secondary electric field coincides with that of the horizontal component of the primary electric field. Consequently, the secondary electric field between the pixel electrodes **190** enhances the determination of the tilt directions of the LC molecules **310**.

Since the LCD performs inversion such as dot inversion, column inversion, etc., adjacent pixel electrodes are supplied with data voltages having opposite polarity with respect to the common voltage and thus a secondary electric field between the adjacent pixel electrodes is almost always generated to enhance the stability of the domains.

Since the tilt directions of all domains make an angle of about 45 degrees with the gate lines **121**, which are parallel to or perpendicular to the edges of the panels **100** and **200**, and the 45-degree intersection of the tilt directions and the transmissive axes of the polarizers gives maximum transmittance, the polarizers can be attached such that the transmissive axes of the polarizers are parallel to or perpendicular to the edges of the panels **100** and **200** and it reduces the production cost.

The resistance increase of the data lines **171** due to the curving can be compensated by widening the data lines **171** since distortion of the electric field and increase of the parasitic capacitance due to the increase of the width of the data lines **171** can be compensated by increasing the size of the pixel electrodes **190** and by adapting a thick organic passivation film.

The LCD shown in FIGS. **8-11** can have several modifications.

For example, the pixel electrodes **190** as well as the common electrode **270** may have cutouts (not shown) for generating fringe field. Furthermore, the cutouts may be substituted with protrusions disposed on the common electrode **270** or the pixel electrodes **190**.

The shapes and the arrangements of the cutouts **272** or the protrusions and the notches **277** may be varied depending on the design factors such as the size of pixels **190**, the ratio of the transverse edges and the longitudinal edges of the pixel electrodes **190**, the type and characteristics of the liquid crystal layer **300**, and so on.

While the present invention has been described in detail with reference to the preferred embodiments, those skilled in the art will appreciate that various modifications and substitutions can be made thereto without departing from the spirit and scope of the present invention as set forth in the appended claims.

What is claimed is:

1. A liquid crystal display comprising;
 - a first substrate;
 - a plurality of pixel electrodes formed on the first substrate;
 - a second substrate;
 - a common electrode formed on the second substrate; and
 - a liquid crystal layer interposed between the first substrate and the second substrate,
 wherein at least one of the pixel electrode and the common electrode have a plurality of tilt direction determining members and at least one of the tilt direction determining members is a cutout and comprises an oblique portion having a pair of notches facing each other.
2. The liquid crystal display of claim 1, wherein at least one of the tilt direction determining members comprises a protrusion.
3. The liquid crystal display of claim 2, wherein the protrusion has a height being the same as or less than the width of the tilt direction determining members.
4. The liquid crystal display of claim 3, wherein the tilt direction determining members has a width ranging about 8-10 microns.
5. The liquid crystal display of claim 1, wherein at least one of the tilt direction determining members comprises a protrusion or a depression.
6. The liquid crystal display of claim 1, wherein the notches are convex or concave.
7. The liquid crystal display of claim 1, wherein the notches are triangular, rectangular, trapezoidal, or semicircular.
8. The liquid crystal display of claim 1, wherein the tilt direction determining member has inversion symmetry with respect to a straight line bisecting the pixel electrode.
9. The liquid crystal display of claim 8, wherein the tilt direction determining members comprise two opposite main oblique portions facing each other having the notches, and the notches have an edge oblique to or perpendicular to the main oblique portions.
10. The liquid crystal display of claim 9, wherein the liquid crystal layer has negative anisotropy and subjected to a vertical alignment.
11. The liquid crystal display of claim 10, further comprising:
 - a first signal line formed on the first substrate;
 - a second signal line formed on the first substrate and intersecting the first signal line;
 - a thin film transistor connected to the first and the second signal lines and the pixel electrode;
 - a common electrode formed on the second substrate; and
 - first and second polarizers disposed on the first and the second substrates and having crossed transmissive axes, wherein the transmissive axis of one of the polarizers are parallel to the first signal line.
12. The liquid crystal display of claim 1, wherein the notches are configured to generate a secondary horizontal field component.

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[标]申请(专利权)人(译)	SONG JANG KUN JUN SAHNG IK 全在HONG 李廷YOUNG LEE JAE HO		
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摘要(译)

提供一种液晶显示器，包括：第一基板；形成在第一基板上的第一信号线；第二信号线，形成在第一基板上并与第一信号线交叉；薄膜晶体管，连接到第一和第二信号线；像素电极连接到薄膜晶体管；第二基板；形成在第二基板上的公共电极；介于第一基板和第二基板之间的液晶层；倾斜方向确定构件形成在第一和第二基板中的一个上并具有凹口。

